

AMENDMENTS TO THE CLAIMS:

Claims 1-23 (cancelled).

24. (New) A method for plating a substrate, comprising:
providing a substrate having fine trench patterns which are covered with a seed layer;
disposing said substrate adjacent an anode such that said substrate and said anode face one another and define a plating space therebetween;
supplying a plating liquid into said plating space, said plating liquid containing metal ions and an additive so as to have an initial additive concentration; and
forming a plated film on a surface of said seed layer by
(i) applying an electric current between said seed layer and said anode while said plating liquid having said initial additive concentration is in said plating space, and
(ii) while continuing to apply said electric current between said seed layer and said anode, changing the additive concentration of said plating liquid in said plating space relative to said initial additive concentration by supplying a liquid into said plating space.

25. (New) The method according to claim 24, wherein
forming a plated film on a surface of said seed layer comprises forming a plated film which extends from a surface of said substrate substantially an equal distance for an entirety of said surface of said substrate.

26. (New) The method according to claim 25, wherein
changing the additive concentration of said plating liquid in said plating space relative to said initial additive concentration by supplying a liquid into said plating space comprises changing said additive concentration of said plating liquid in said plating space relative to said initial additive concentration by intermittently supplying said plating liquid into said plating space.

27. (New) The method according to claim 26, wherein changing said additive concentration of said plating liquid in said plating space relative to said initial additive concentration by intermittently supplying said plating liquid into said plating space comprises lowering said additive concentration of said plating liquid in said plating space relative to said initial additive concentration by intermittently supplying said plating liquid into said plating space.

28. (New) The method according to claim 27, wherein lowering said additive concentration of said plating liquid in said plating space relative to said initial additive concentration comprises

(i) lowering said additive concentration of said plating liquid to a first level during a mid stage of the forming of the plated film on said seed layer, and

(ii) lowering said additive concentration of said plating liquid to a second level, which is lower than said first level, during a stage of the forming of the plated film on said seed layer that is subsequent to said mid stage.

29. (New) The method according to claim 28, wherein said additive comprises a brightener.

30. (New) The method according to claim 26, wherein changing said additive concentration of said plating liquid in said plating space relative to said initial additive concentration by intermittently supplying said plating liquid into said plating space comprises raising said additive concentration of said plating liquid in said plating space relative to said initial additive concentration by intermittently supplying said plating liquid into said plating space.

31. (New) The method according to claim 30, wherein raising said additive concentration of said plating liquid in said plating space relative to said initial additive concentration comprises

(i) raising said additive concentration of said plating liquid to a first level during a mid stage of the forming of the plated film on said seed layer, and

(ii) raising said additive concentration of said plating liquid to a second level, which is higher than said first level, during a stage of the forming of the plated film on said seed layer that is subsequent to said mid stage.

32. (New) The method according to claim 31, wherein said additive comprises a leveler.

33. (New) The method according to claim 25, wherein changing the additive concentration of said plating liquid in said plating space relative to said initial additive concentration by supplying a liquid into said plating space comprises changing said additive concentration of said plating liquid in said plating space relative to said initial additive concentration by introducing into said plating space a solution or a plating liquid having an additive concentration that is different than said initial additive concentration.

34. (New) The method according to claim 33, wherein changing said additive concentration of said plating liquid in said plating space relative to said initial additive concentration by introducing into said plating space a solution or a plating liquid having an additive concentration that is different than said initial additive concentration comprises lowering said additive concentration of said plating liquid in said plating space relative to said initial additive concentration by introducing into said plating space a solution or a plating liquid having an additive concentration that is different than said initial additive concentration.

35. (New) The method according to claim 34, wherein lowering said additive concentration of said plating liquid in said plating space relative to said initial additive concentration comprises

(i) lowering said additive concentration of said plating liquid to a first level during a mid stage of the forming of the plated film on said seed layer, and

(ii) lowering said additive concentration of said plating liquid to a second level, which is lower than said first level, during a stage of the forming of the plated film on said seed layer that is subsequent to said mid stage.

36. (New) The method according to claim 35, wherein
said additive comprises a brightener.

37. (New) The method according to claim 33, wherein
changing said additive concentration of said plating liquid in said plating space relative to said initial additive concentration by introducing into said plating space a solution or a plating liquid having an additive concentration that is different than said initial additive concentration comprises raising said additive concentration of said plating liquid in said plating space relative to said initial additive concentration by introducing into said plating space a solution or a plating liquid having an additive concentration that is different than said initial additive concentration.

38. (New) The method according to claim 37, wherein
raising said additive concentration of said plating liquid in said plating space relative to said initial additive concentration comprises

(i) raising said additive concentration of said plating liquid to a first level during a mid stage of the forming of the plated film on said seed layer, and

(ii) raising said additive concentration of said plating liquid to a second level, which is higher than said first level, during a stage of the forming of the plated film on said seed layer that is subsequent to said mid stage.

39. (New) The method according to claim 38, wherein
said additive comprises a leveler.